

SCOPE: **+5V/Programmable Low-Dropout Voltage Regulator**

<u>Device Type</u>	<u>Generic Number</u>
01	MAX667M(x)/883B

Case Outline(s). The case outlines shall be designated in Mil-Std-1835 and as follows:

<u>Outline Letter</u>	<u>Mil-Std-1835</u>	<u>Case Outline</u>	<u>Package Code</u>
MAXIM SMD			
JA P	GDIP1-T8 or CDIP2-T8	8 LEAD Cerdip	J8

Absolute Maximum Ratings

Input Supply Voltage	+18V
Output Short Circuit to GND	1 sec
LBO Output Sink Current	50mA
LBO Output Voltage	GND to V_{OUT}
SHDN Input Voltage	-0.3V to $(V_{IN}+0.3)V$
Input Voltages LBI, SET	-0.3V to $(V_{IN}-1.0)V$
Lead Temperature (soldering, 10 seconds)	+300°C
Storage Temperature	-65°C to +150°C
Continuous Power Dissipation	$T_A=+70^{\circ}C$
8 lead Cerdip(derate 8.0mW/°C above +70°C)	640mW
Junction Temperature T_J	+150°C
Thermal Resistance, Junction to Case, θ_{JC} :	55°C/W
Thermal Resistance, Junction to Ambient, θ_{JA} :	125°C/W

Recommended Operating Conditions.

Ambient Operating Range (T_A)	-55°C to +125°C
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Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TABLE 1 ELECTRICAL TESTS

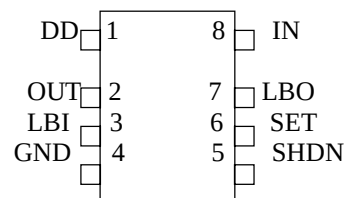
PARAMETER	Symbol	CONDITIONS -55 °C ≤ T _A ≤ +125 °C GND=0V, V _{IN} =+9V, V _{OUT} =+5V Unless otherwise specified	Group A Subgroup	Device type	Limits Min	Limits Max	Units
Input Voltage	V _{IN}		1,2,3	01	3.5	16.5	V
Output Voltage	V _{OUT}	V _{SET} =0V, V _{IN} =6V, I _{OUT} =10mA	1,2,3	01	4.8	5.2	V
Maximum Output Current	I _{OUT}	V _{IN} =6V, 4.5V < V _{OUT} < 5.5V	1,2,3	01	250		mA
Quiescent Current	I _Q	V _{SHDN} =2V	1 2,3	01		1 2	μA
		V _{SHDN} =0V, V _{SET} =0V, I _{OUT} =0μA	1 2,3	01		25 35	
		V _{SHDN} =0V, V _{SET} =0V, I _{OUT} =100μA	1 2,3	01		30 50	
		V _{SHDN} =0V, V _{SET} =0V, I _{OUT} =200μA	1 2,3	01		15 20	mA
Dropout Voltage NOTE 1		I _{OUT} =100μA	1 2,3	01		60 75	mV
		I _{OUT} =200μA	1 2,3	01		250 350	
Load Regulation		10mA ≤ I _{OUT} ≤ 200mA	1 2,3	01		100 250	mV
Line Regulation NOTE 2		6.0V ≤ V _{IN} ≤ 10V, I _{OUT} =10mA	1 2,3	01		10 15	mV
Set Reference Voltage	V _{SET}		1,2,3	01	1.20	1.28	V
Set Input Leakage Current	I _{SET}	V _{SET} =1.5V	1 2,3	01		±10 ±1000	nA
Output Leakage Current	I _{OUT}	V _{SHDN} =2V	1,2,3	01		1	μA
Short-Circuit Current	I _{OUT}	NOTE 3	1 2,3	01		400 450	mA
Low-Battery Detector Reference Voltage	V _{LBI}		1,2,3	01	1.185	1.295	V
Low-Battery Detector Input Leakage Current	I _{LBI}	V _{LBI} =1.5V	1 2,3	01		±10 ±1000	nA
Low-Battery Detector Output Voltage	V _{LBO}	V _{IN} =9V, V _{LBI} =2V, I _{LBO} =10mA	1 2,3	01		0.25 0.40	V
Shutdown Threshold	V _{SHDN}		1,2,3	01	1.5		V
Shutdown Input Leakage Current	I _{SHDN}	V _{SHDN} = 0 to V _{IN}	1 2,3	01		±10 ±1000	nA
Dropout Detector Output Voltage	V _{DD}	V _{SET} =0V, V _{SHDN} =0V, R _{DD} =100kΩ, V _{IN} =7V, I _{OUT} =10mA	1,2,3	01		0.25	V
		V _{SET} =0V, V _{SHDN} =0V, R _{DD} =100kΩ, V _{IN} =4.5V, I _{OUT} =10mA			4		

NOTE 1: Dropout voltage is $V_{IN} - V_{OUT}$ when V_{OUT} falls to 0.1V below its value at $V_{IN} = V_{OUT} + 2V$.

NOTE 2: Line Regulation Limit = .05%/V for Subgroup 1 and .075 %/V for Subgroup 2,3.

NOTE 3: Short-Circuit Current is pulsed tested to maintain junction temperature. Short-circuit duration is limited by package dissipation.

01 ORDERING INFORMATION. SMD PKG.Code
 MAX667MJA/883B 5962-9212604MPA J08



TERMINAL NUMBER	FUNCTION	MAX 667 MJA
1	Dropout Detector Output - the collector of a PNP pass transistor. Normally an open circuit, it sources current as dropout is reached.	DD
2	Regulated Output Voltage. OUT falls to 0V when SHDN is above 1.5V. SET determines output voltage when SET is above 50mV; otherwise it is 5V. OUT must be connected to an output filter capacitor.	OUT
3	Low-Battery Detector. A CMOS input to an internal 1.255V comparator whose output is the LBO pin.	LBI
4	Ground.	GND
5	Shutdown Input. Connected to GND for normal operation (output active). Pull above 1.5V to disable OUT, LBO, and DD and to reduce quiescent current to <1μA.	SHDN
6	(Output) Voltage Set, CMOS Input. Connect to GND for 5V output. For other voltages, connect external resistive divider from OUT.	SET
7	Low-Battery Output. An open-drain N-channel transistor that sinks current to GND when LBI is less than 1.22V.	LBO
8	Positive Input Voltage (unregulated)	IN

QUALITY ASSURANCE

Sampling and inspection procedures shall be in accordance with MIL-Prf-38535, Appendix A as specified in Mil-Std-883.

Screening shall be in accordance with Method 5004 of Mil-Std-883. Burn-in test Method 1015:

1. Test Condition, A, B, C, or D.
2. TA = +125°C minimum.
3. Interim and final electrical test requirements shall be specified in Table 2.

Quality conformance inspection shall be in accordance with Method 5005 of Mil-Std-883, including Groups A, B, C, and D inspection.

Group A inspection:

1. Tests as specified in Table 2.
2. Selected subgroups in Table 1, Method 5005 of Mil-Std-883 shall be omitted.

Group C and D inspections:

- a. End-point electrical parameters shall be specified in Table 1.
- b. Steady-state life test, Method 1005 of Mil-Std-883:
 1. Test condition A, B, C, D.
 2. TA = +125°C, minimum.
 3. Test duration, 1000 hours, except as permitted by Method 1005 of Mil-Std-883.

TABLE 2. ELECTRICAL TEST REQUIREMENTS

Mil-Std-883 Test Requirements	Subgroups per Method 5005, Table 1
Interim Electric Parameters Method 5004	1
Final Electrical Parameters Method 5005	1*, 2, 3
Group A Test Requirements Method 5005	1, 2, 3
Group C and D End-Point Electrical Parameters Method 5005	1

* PDA applies to Subgroup 1 only.